

EP 2812
S

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:
 KINOSHITA, H., et al.
 Serial No: 08/808,315
 Filed: February 27, 1997
 For: SAPPHIRE MONOCRYSTAL,
 SEMICONDUCTOR LASER DIODE
 USING THE SAME FOR
 SUBSTRATE, AND METHOD FOR
 MANUFACTURING THE SAME

Art Unit: 2812
 Examiner: CHANG, Y.



Assistant Commissioner for Patents
 Washington, D.C. 20231

Dear Sir:

Transmitted herewith is an amendment in the above-identified application.

- Small entity status of this application under 37 C.F.R. §§ 1.9 & 1.27 has been established by a verified statement previously submitted.
- A verified statement to establish small entity status under 37 C.F.R. §§ 1.9 & 1.27 is enclosed.
- A certified copy of _____ Patent Application No. _____ filed _____ from which priority is claimed under 35 U.S.C. § 119 is enclosed.

The fee has been calculated as shown below:

	(Col. 1) CLAIMS REMAINING AFTER AMENDMENT		(Col. 2) HIGHEST NUMBER PREVIOUSLY PAID FOR	(Col. 3) PRESENT EXTRA*	LG/SM \$ ENTITY FEE		ADD'L FEE DUE
TOTAL CLAIMS FEE	5	-	20	**	0	LG=\$18 SM=\$9	\$18
INDEPENDENT CLAIMS FEE	3	-	3	***	0	LG=\$78 SM=\$39	\$78
FIRST PRESENTATION OF MULTIPLE DEPENDENT CLAIMS						LARGE ENTITY FEE = \$260 SMALL ENTITY FEE = \$130	\$0
						TOTAL	\$0

* If the entry in Col. 1 is less than the entry in Col. 2, write "0" in Col. 3.

** If the "Highest Number Previously Paid For" IN THIS SPACE is less than 20, write "20" in this space.

*** If the "Highest Number Previously Paid For" IN THIS SPACE is less than 3, write "3" in this space. The "Highest Number Previously Paid For" (Total or Independent) is the highest number found from the equivalent box on Col. 1 of a prior amendment or the number of claims originally filed.

- A check in the amount of \$ 0 to cover the additional claims fee is enclosed. **A copy of this sheet is enclosed.**
- A check in the amount of \$ 110 to cover the extension fee is enclosed. **A copy of this sheet is enclosed.**
- The Commissioner is hereby authorized to charge any deficiencies of fees associated with this communication or credit any overpayment to Deposit Account No. 12-1820. **A copy of this sheet is enclosed.**
 - Any filing fees under 37 C.F.R. § 1.16 for the presentation of extra claims
 - Any patent application processing fees under 37 C.F.R. § 1.17

Respectfully submitted,
 LOEB & LOEB LLP

By:

John P. Scherlacher
 Registration No. 23,009
 Attorney for Applicant(s)

Date: September 23, 1999

TC 2500 MAIL ROOM

RECEIVED
SEP 23 1999

10100 Santa Monica Blvd., 22nd Floor
 Los Angeles, California 90067-4164
 Telephone: 310-282-2000
 Facsimile: 310-282-2192



PATENT
0247D-5385

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Hiroyuki Kinoshita et al.

Serial No: 08/808,315

Filed: February 27, 1997

For: Sapphire Monocrystal, Semiconductor
Laser Diode Using the Same for
Substrate, and Method for
Manufacturing the Same

Art Unit: 2812

Examiner: Yoni Y. Chang

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to:

Assistant Commissioner for Patents
Washington D.C. 20231, on

September 23, 1999

Date of Deposit

John P. Scherlacher

Name

John P. Scherlacher 09/23/99

Signature

Date

AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

In response to the Office Action dated June 4, 1999, please amend the above-referenced application as follows:

IN THE SPECIFICATION:

On page 9, line 13, delete "is widely" and insert --may be--.

IN THE CLAIMS:

Please cancel claims 1-8 and add new claims 17-21 as follows:

C) *sub* 17. A tool comprising a sapphire monocrystal body having a sharp edge formed by a working plane and a cleavage plane parallel to a plane R of the sapphire monocrystal.

18. A semiconductor device comprising:

a substrate formed of a sapphire monocrystal, the substrate having a major face and a side face, the side face being a cleavage plane parallel to a plane R of the sapphire monocrystal; and a semiconductor element formed on the major face of the sapphire substrate.

RECEIVED
TC 2500 MAIL ROOM
SEP 23 1999